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FAIRCHILD

SEMICONDUCTOR®

December 2013

FQAF11N90C N-Channel QFET[®] MOSFET

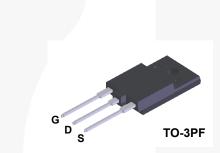
900 V, 7.0 A, 1.1 Ω

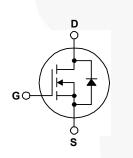
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 7.0 A, 900 V, $R_{DS(on)}$ = 1.1 Ω (Max.) @ V_{GS} = 10 V, I_D = 3.5 A
- Low Gate Charge (Typ. 60 nC)
- Low Crss (Typ. 23 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

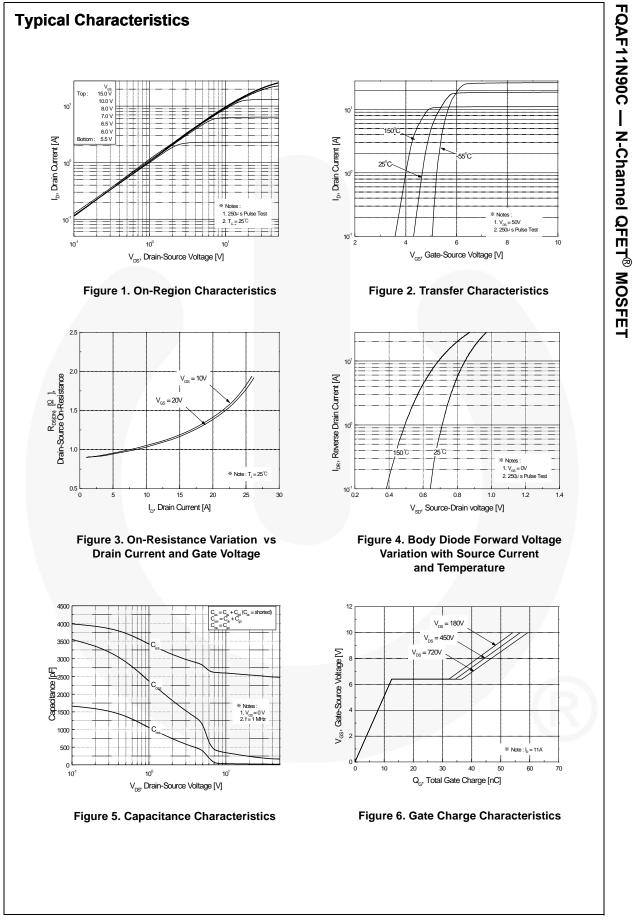
Symbol	Parameter		FQAF11N90C	Unit
V _{DSS}	Drain-Source Voltage		900	V
ID	Drain Current - Continuous ($T_C = 25^{\circ}C$)		7.0	A
	- Continuous (T _C = 100°C)		4.4	A
I _{DM}	Drain Current - Pulsed	Note 1)	28.0	A
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	Note 2)	960	mJ
I _{AR}	Avalanche Current	Note 1)	7.0	A
E _{AR}	Repetitive Avalanche Energy	Note 1)	12	mJ
dv/dt	Peak Diode Recovery dv/dt	Note 3)	4.0	V/ns
PD	Power Dissipation (T _C = 25°C)		120	W
	- Derate above 25°C		0.96	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
Τ _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.		300	°C

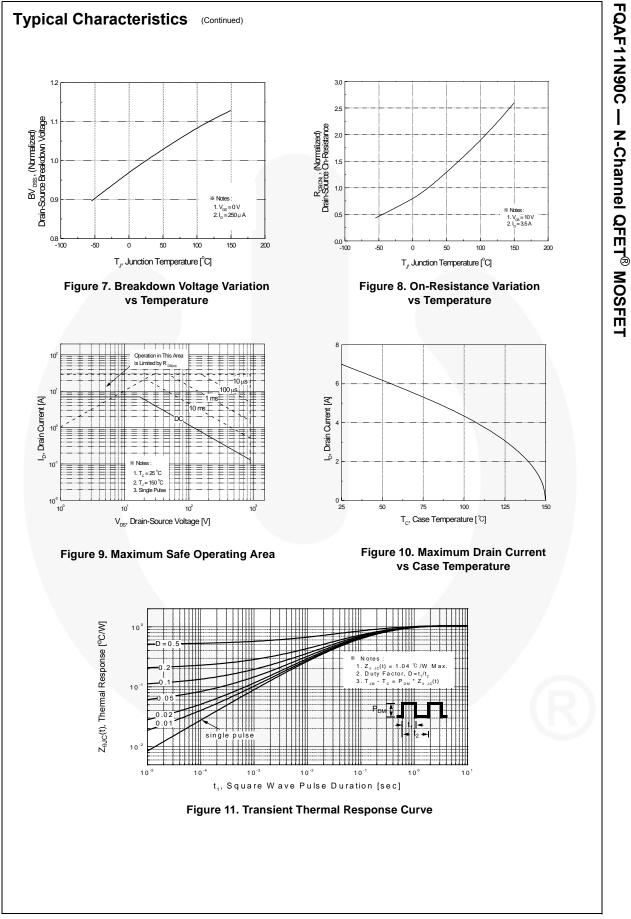
Thermal Characteristics

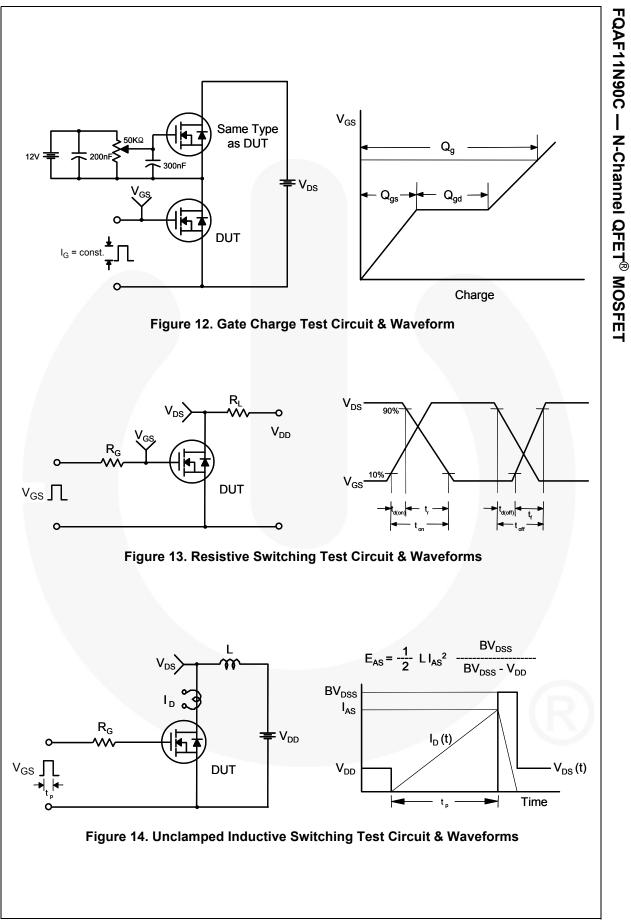
Symbol	Parameter	FQAF11N90C	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case, Max.	1.04	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W

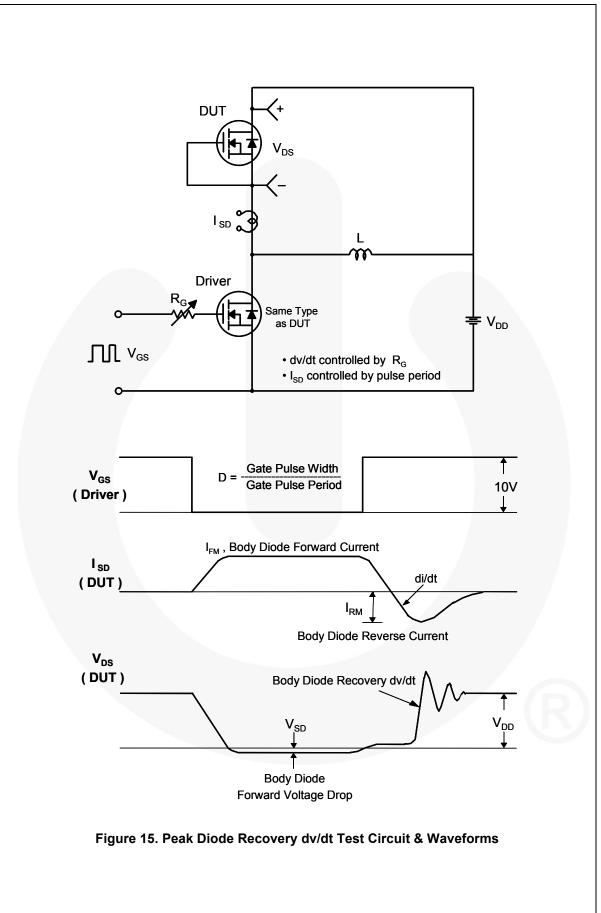
	Number	Top Mark	Packa	ige	Packing Method	d Reel	Size	Tape W	idth	Quantity
FQAF	11N90C	FQAF11N90C	TO-3F	PF	Tube	N	/A	N/A		30 units
lectri	cal Cha	racteristics	T _C = 25°C u	unless other	wise noted.					
Symbol		Parameter			Test Conditions		Min.	Тур.	Max.	Unit
Off Cha	racterist	ics								
BV _{DSS}	Drain-Sou	irce Breakdown Volta	age	V _{GS} = 0	V, I _D = 250 μA		900			V
ΔBV_{DSS} / ΔT_{J}	Breakdow Coefficien	n Voltage Temperati t	ure	I _D = 250	μA , Referenced t	o 25°C		1.0		V/°C
I _{DSS}	Zoro Coto	Zero Gate Voltage Drain Current		V _{DS} = 900 V, V _{GS} = 0 V					10	μA
					20 V, T _C = 125°C				100	μA
I _{GSSF}	Gate-Bod	y Leakage Current, I			$V, V_{DS} = 0 V$				100	nA
I _{GSSR}	Gate-Bod	y Leakage Current, I	Reverse	V _{GS} = -3	0 V, V _{DS} = 0 V				-100	nA
On Cha	racterist	ics								
V _{GS(th)}	Gate Thre	shold Voltage		$V_{DS} = V_{C}$	_{GS} , I _D = 250 μA		3.0		5.0	V
R _{DS(on)}	Static Dra On-Resist			V _{GS} =10	V, I _D =3.5 A			0.91	1.1	Ω
9 _{FS}	Forward T	ransconductance		V _{DS} = 50) V, I _D = 3.5 A					S
	ł									
Dvnam	ic Charad	cteristics								
Dynam C _{iss}	ic Charac	cteristics acitance		Vpc = 25	$i \vee V_{cc} = 0 \vee$			2530	3290	pF
-	Input Cap			V _{DS} = 25 f = 1.0 M	5 V, V _{GS} = 0 V, Hz			2530 215	3290 280	pF pF
C _{iss} C _{oss}	Input Cap Output Ca	acitance								-
C _{iss} C _{oss} C _{rss}	Input Cap Output Ca Reverse T	acitance apacitance Fransfer Capacitance						215	280	pF
C _{iss} C _{oss} C _{rss} Switchi	Input Cap Output Ca Reverse T	acitance apacitance	e	f = 1.0 M	Hz			215	280	pF
C _{iss} C _{oss} C _{rss} Switchi	Input Cap Output Ca Reverse T	acitance apacitance Fransfer Capacitance acteristics Delay Time	e	f = 1.0 M V _{DD} = 45	Hz 50 V, I _D = 11.0 A,			215 23	280 30	pF pF
C _{iss} C _{oss} C _{rss} Switchi t _{d(on)} t _r	Input Cap Output Ca Reverse T ng Chara Turn-On E Turn-On F	acitance apacitance Fransfer Capacitance acteristics Delay Time	e	f = 1.0 M	Hz 50 V, I _D = 11.0 A,			215 23 60	280 30 130	pF pF ns
$\frac{C_{iss}}{C_{oss}}$ $\frac{C_{rss}}{Switchi}$ $\frac{t_{d(on)}}{t_r}$ $\frac{t_{d(off)}}{t_{d(off)}}$	Input Cap Output Ca Reverse T ng Chara Turn-On E Turn-On F	acitance apacitance Transfer Capacitance acteristics Delay Time Rise Time Delay Time	e	f = 1.0 M V _{DD} = 45	Hz 50 V, I _D = 11.0 A,	(Note 4)	 	215 23 60 130	280 30 130 270	pF pF ns ns
$\frac{C_{iss}}{C_{oss}}$ $\frac{C_{rss}}{Switchi}$ $\frac{t_{d(on)}}{t_r}$ $\frac{t_{d(off)}}{t_f}$	Input Cap Output Ca Reverse T ng Chara Turn-On E Turn-On F Turn-Off E	acitance apacitance fransfer Capacitance acteristics Delay Time Rise Time Delay Time Fall Time	9	f = 1.0 M V _{DD} = 45 R _G = 25	Hz 50 V, I _D = 11.0 A, Ω	(Note 4)	 	215 23 60 130 130	280 30 130 270 270	pF pF ns ns ns
C_{iss} C_{oss} C_{rss} $Switchi$ $t_{d(on)}$ t_{r} $t_{d(off)}$ t_{f} Q_{g}	Input Cap Output Ca Reverse T ing Chara Turn-On E Turn-On F Turn-Off E Turn-Off F Total Gate	acitance apacitance fransfer Capacitance acteristics Delay Time Rise Time Delay Time Fall Time	e	f = 1.0 M $V_{DD} = 45$ $R_G = 25$ $V_{DS} = 72$	Hz 50 V, I _D = 11.0 A, Ω	(Note 4)	 	215 23 60 130 130 85	280 30 130 270 270 180	pF pF ns ns ns ns
C_{iss} C_{oss} C_{rss} Switch i $t_{d(on)}$ t_{r} $t_{d(off)}$ t_{f} Q_{g} Q_{gs}	Input Cap Output Ca Reverse T ing Chara Turn-On E Turn-On F Turn-Off E Turn-Off F Total Gate	acitance apacitance Fransfer Capacitance acteristics Delay Time Rise Time Delay Time Fall Time Charge rce Charge	e	f = 1.0 M V _{DD} = 45 R _G = 25	Hz 50 V, I _D = 11.0 A, Ω	(Note 4) (Note 4)	 	215 23 60 130 130 85 60	280 30 130 270 270 180 80	pF pF ns ns ns ns nc
$\begin{array}{c} C_{iss} \\ C_{oss} \\ C_{rss} \end{array}$	Input Cap Output Ca Reverse 1 ng Chara Turn-On E Turn-Off E Turn-Off F Turn-Off F Total Gate Gate-Sour Gate-Drai	acitance apacitance Transfer Capacitance acteristics Delay Time Rise Time Delay Time Fall Time e Charge rce Charge n Charge	9	f = 1.0 M $V_{DD} = 45$ $R_G = 25$ $V_{DS} = 72$ $V_{GS} = 10$	Hz 50 V, I _D = 11.0 A, Ω 20 V, I _D = 11.0 A,) V		 	215 23 60 130 130 85 60 13	280 30 130 270 270 180 80 	pF pF ns ns ns nC nC
C_{iss} C_{oss} C_{rss} Switchi $t_{d(on)}$ t_r $t_{d(off)}$ t_f Q_g Q_{gs} Q_{gd} Drain-S	Input Cap Output Ca Reverse 1 Ing Chara Turn-On E Turn-Off E Turn-Off F Total Gate Gate-Soui Gate-Drai	acitance apacitance Transfer Capacitance acteristics Delay Time Rise Time Delay Time Fall Time e Charge roe Charge n Charge	e stics and	f = 1.0 M $V_{DD} = 45$ $R_G = 25$ $V_{DS} = 72$ $V_{GS} = 10$ d Maxin	Hz 50 V, I _D = 11.0 A, Ω 20 V, I _D = 11.0 A,) V mum Ratings		 	215 23 60 130 130 85 60 13	280 30 130 270 270 180 80 	pF pF ns ns ns nC nC nC
$\begin{array}{c} C_{iss} \\ C_{oss} \\ C_{rss} \end{array}$	Input Cap Output Ca Reverse T ing Chara Turn-On E Turn-On F Turn-Off E Turn-Off F Total Gate Gate-Soui Gate-Drai	acitance apacitance Fransfer Capacitance acteristics Delay Time Rise Time Delay Time Fall Time Charge rce Charge n Charge n Charge	e s s s tics and Source Diod	$f = 1.0 M$ $V_{DD} = 4\xi$ $R_G = 25$ $V_{DS} = 72$ $V_{GS} = 10$ $d Maxin$ $d Forwar$	Hz 50 V, I _D = 11.0 A, Ω 20 V, I _D = 11.0 A,) V mum Ratings rd Current		 	215 23 60 130 130 85 60 13 25	280 30 130 270 270 180 80 7.0	pF pF ns ns ns nc nC nC A
$\begin{array}{c} C_{iss} \\ C_{oss} \\ C_{rss} \\ \end{array} \\ \begin{array}{c} \textbf{Switchi} \\ \textbf{t}_{d(on)} \\ \textbf{t}_{r} \\ \textbf{t}_{d(off)} \\ \textbf{t}_{f} \\ \textbf{Q}_{g} \\ \textbf{Q}_{gs} \\ \textbf{Q}_{gd} \\ \end{array} \\ \begin{array}{c} \textbf{Drain-S} \\ \textbf{I}_{S} \\ \textbf{I}_{SM} \\ \end{array} \end{array}$	Input Cap Output Ca Reverse T ing Chara Turn-On E Turn-On F Turn-Off E Turn-Off F Total Gate Gate-Sour Gate-Drai Source Di Maximum	acitance apacitance Fransfer Capacitance acteristics Delay Time Rise Time Delay Time Fall Time Charge rce Charge n Charge n Charge ode Characteri Continuous Drain-S Pulsed Drain-Source	stics and source Diode Fo	$f = 1.0 M$ $V_{DD} = 45$ $R_{G} = 25$ $V_{DS} = 72$ $V_{GS} = 10$ $d Maxiii$ In Forward Cu	Hz $(50 V, I_D = 11.0 A, \Omega)$ $(20 V, I_D = 11.0 A, \Omega)$ $(20 V, I_D = 11.0 A, \Omega)$ The second se		 	215 23 60 130 130 85 60 13 25	280 30 130 270 270 180 80 	pF pF ns ns ns nC nC nC
C_{iss} C_{oss} C_{rss} Switch i $t_{d(on)}$ t_r $t_{d(off)}$ t_f Q_g Q_{gs} Q_{gd} Drain-S I_s	Input Cap Output Ca Reverse T ng Chara Turn-On E Turn-Off E Turn-Off F Total Gate Gate-Sour Gate-Drai Source Di Maximum Maximum Drain-Sou	acitance apacitance Fransfer Capacitance acteristics Delay Time Rise Time Delay Time Fall Time Charge rce Charge n Charge n Charge	stics and source Diod ce Diode Fo Voltage	$f = 1.0 \text{ M}$ $V_{DD} = 45$ $R_G = 25$ $V_{DS} = 72$ $V_{GS} = 10$ $d \text{ Maxiii}$ $e \text{ Forwar}$ $rward Cu$ $V_{GS} = 0$	Hz 50 V, I _D = 11.0 A, Ω 20 V, I _D = 11.0 A,) V mum Ratings rd Current		 	215 23 60 130 130 85 60 13 25 	280 30 270 270 180 80 7.0 28.0	pF pF ns ns ns nc nC nC A

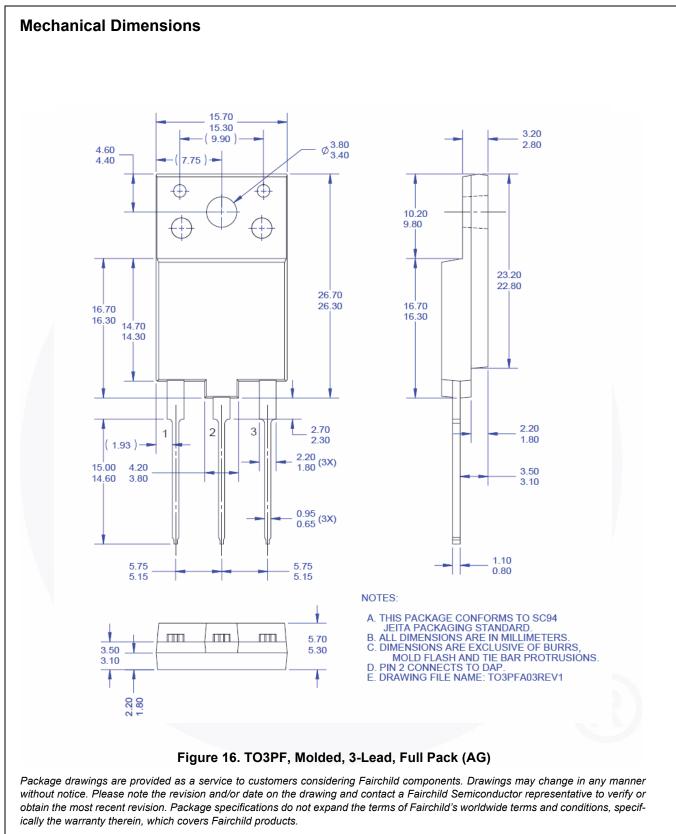
Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 37 mH, I_{AS} = 7.0 Å, V_{DD} = 50 V, R_{G} = 25 Ω , starting T_{J} = 25°C. 3. $I_{SD} \le 11.0$ Å, di/dt ≤ 200 Å/µs, $V_{DD} \le BV_{DSS}$ starting T_{J} = 25°C. 4. Essentially independent of operating temperature.











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FQAF11N90C ---

N-Channel QFET[®] MOSFET



Not In Production

Obsolete

Datasheet contains specifications on a product that is discontinued by Fairchild

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Rev. 166

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